SILICON (Si) POWER MOSFET A CEU16N10L



CEU16N10L

100V ▲ 95mΩ ▲ 13.3A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO252 (DPAK) package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability





RoHS

REACH

MAXIMUM RATINGS

Parameter (T_c = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	100V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at T _c = 25°C	Ι _D	13.3A
Continuous Drain Current at T _c = 100°C	Ι _D	9.5A
Pulsed Drain Current Note 1	IDM Note4	53A
Maximum Power Dissipation at T _c = 25°C	PD	43W
Power Dissipation Derating above 25°C	ΔP _D	0.34W/°C
Single Pulsed Avalanche Energy Note 4	E _{AS}	44.2mJ
Single Pulsed Avalanche Current Note 4	I _{AS}	13.3A
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

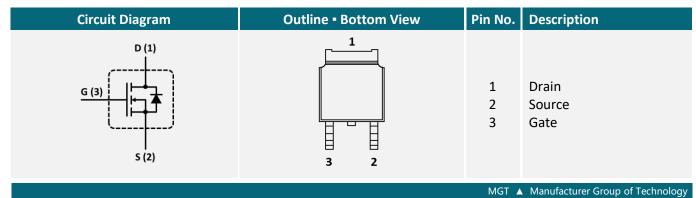
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	3.5°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{th_ja}	50°C/W

APPLICATIONS

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+ 4 -	50			

PIN DESCRIPTION



CEU16N10L A Rev.001 A Date: 30/09/2022 A Page: 1

Copyright by MGT A www.mgt.co.com A All rights reserved A The information in this document is subject to change without notice.



ELECTRICAL CHARACTERISTICS A T_c = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	100			V
Zero Gate Voltage Drain Current	V_{DS} = 100V, V_{GS} = 0V	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	V _{GS(th)}	1		3	V
Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 6.5A	R _{DS(ON)}		95	115	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 5V$, $I_D = 5A$	R _{DS(ON)}		100	125	mΩ
Dynamic Characteristics Note 3						
Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{ISS}		630		рF
Output Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	Coss		105		рF
Reverse Transfer Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{RSS}		26		pF
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 13.3A, $R_{\text{G}(\text{ext})}$ = 25 Ω	t _{D(ON)}		11		ns
Turn-On Rise Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 13.3A, $R_{\text{G}(\text{ext})}$ = 25 Ω	t _R		2.7		ns
Turn-Off Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 13.3A, $R_{\text{G}(\text{ext})}$ = 25 Ω	$t_{D(OFF)}$		73		ns
Turn-Off Fall Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 13.3A, $R_{\text{G}(\text{ext})}$ = 25 Ω	t _F		7.5		ns
Total Gate Charge	V_{DS} = 80V, V_{GS} = 10V, I_{D} = 13.3A	Q_{G}		17		nC
Gate Source Charge	V_{DS} = 80V, V_{GS} = 10V, I_{D} = 13.3A	Q _{GS}		2.2		nC
Gate Drain Charge	V_{DS} = 80V, V_{GS} = 10V, I_{D} = 13.3A	\mathbf{Q}_{GD}		3.5		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		ls			13.3	А
Drain-Source Diode Forward Voltage Note 2	V _{GS} = 0V, I _S = 13.3A	V_{SD}			1.5	V

Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

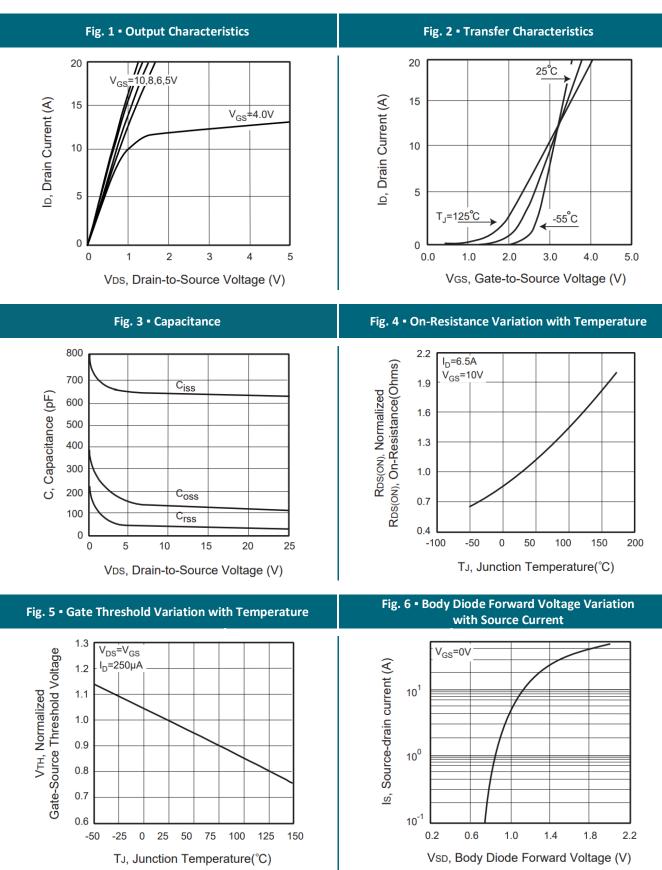
3: Guaranteed by design, not subject to production testing.

4: Pulse width limited by safe operating area.

5: L = 0.5mH, I_{AS} = 13.3A, V_{DD} = 25V, R_G = 25 Ω , Starting T_J = 25°C



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE





REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

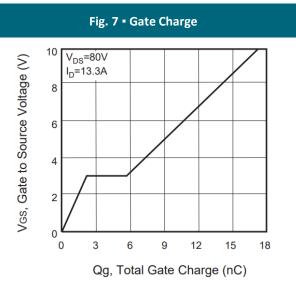


Fig. 9 - Breakdown Voltage Variation vs. Temperature

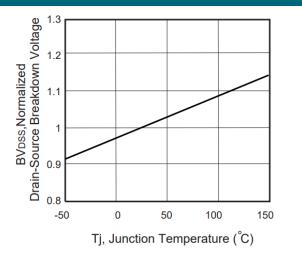
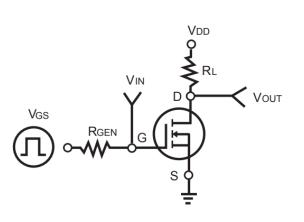


Fig. 10 • Switching Test Circuit



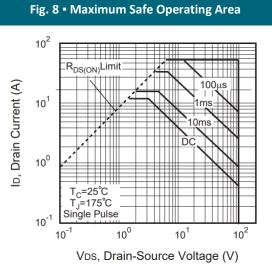
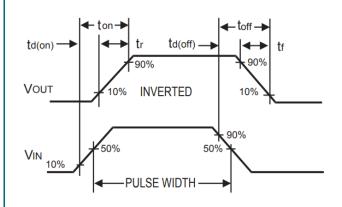


Fig. 11 - Switching Waveforms



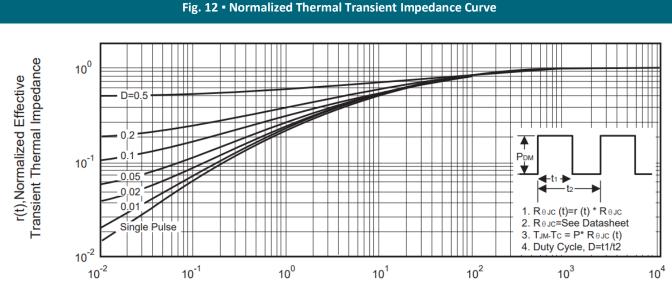
MGT 🔺 Manufacturer Group of Technology

CEU16N10L ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 4

Copyright by MGT **A** www.mgt.co.com **A** All rights reserved **A** The information in this document is subject to change without notice.

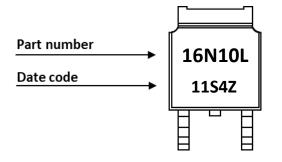


REFERENCE DATA ▲TYPICAL DEVICE PERFORMANCE



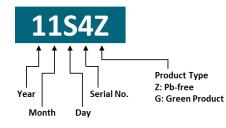
Square Wave Pulse Duration (msec)

PART MARKING



DATE CODE

Example: 11S4Z



Coding list for "Day"									
1	2	3	4	5	6	7	8	9	A
01	02	03	04	05	06	07	08	09	10
B	C	D	E	F	G	H	 	J	K
11	12	13	14	15	16	17	18	19	20
L	M	N	O	P	Q	R	S	T	U
21	22	23	24	25	26	27	28	29	30
V 31									
	01 B 11 L 21 V	01 02 B C 11 12 L M 22 V	01 02 03 B C D 11 12 13 L M N 21 23 23	1 2 3 4 02 03 04 B C D E 12 13 E L M 23 O V V V V	1 2 3 4 5 01 02 03 04 5 B C D E F 11 12 D 24 F 12 N O P 25 V V V V V	1 2 3 4 5 6 01 02 03 04 55 6 B C D E F 6 11 12 D E F 6 L M N O P Q V V V V V V	1 2 3 4 5 6 7 1 02 03 04 5 6 7 B C D E F 6 17 L M N 02 P 26 R V V V V V V V	1 2 3 4 5 6 7 8 01 02 03 04 55 6 7 8 B C D E F G H I 11 12 D E F 5 6 7 8 L N 22 P P Q P 26 P 27 28 V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V V <th>1 2 3 4 5 6 7 8 9 1 02 03 4 5 6 7 8 9 1 12 13 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1</th>	1 2 3 4 5 6 7 8 9 1 02 03 4 5 6 7 8 9 1 12 13 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1

Coding list for "Month"

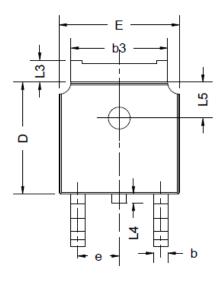


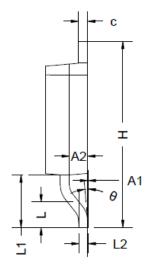
CEU16N10L ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 5

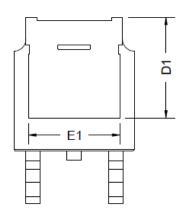
Copyright by MGT ▲ www.mgt.co.com ▲ All rights reserved ▲ The information in this document is subject to change without notice.



PACKAGE OUTLINE







 ł
۷
ŧ

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	2.20	2.30	2.38	е		2.286 BSC	
A1	0.00	-	0.20	Н	9.40	10.10	10.50
A2	0.90	1.07	1.17	L	1.38	1.50	1.75
b	0.68	0.78	0.90	L1		2.90 REF	
b3	5.23	5.33	5.46	L2		0.51 BSC	
С	0.43	0.53	0.61	L3	0.88	-	1.28
D	5.98	6.10	6.22	L4	0.50		1.00
D1		5.30 REF		L5	1.65	1.80	1.95
E	6.40	6.60	6.73	θ	0°	-	8°
E1	4.63	-	-				

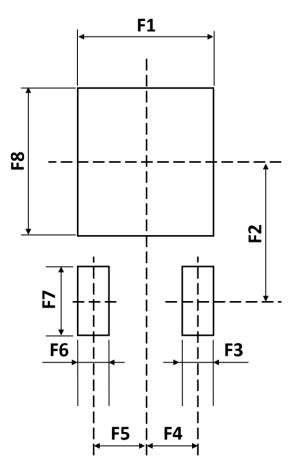
ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEU16N10L	TO252 (DPAK)	Reel	2,500pcs	5,000pcs	40,000pcs	

Copyright by MGT **A** www.mgt.co.com **A** All rights reserved **A** The information in this document is subject to change without notice.



RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	6.00	-	F5	-	2.29	-
F2	-	6.25	-	F6	-	1.40	-
F3	-	1.40	-	F7	-	3.00	-
F4	-	2.29	-	F8	-	6.50	-

Notes:

1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

CEU16N10L ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 7

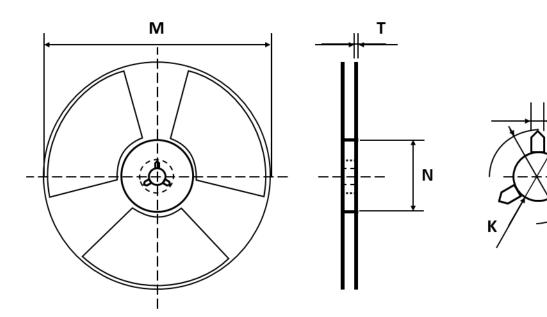


S

Н

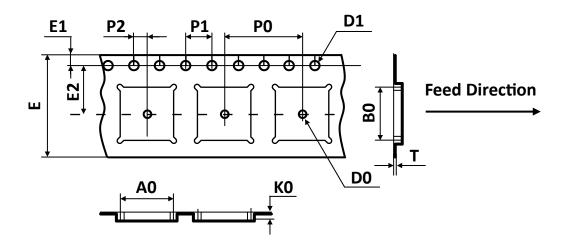


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	N	Т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
16mm	Ø330	±2.00	±0.50	±0.20	±0.50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

TAPE DIMENSIONS All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
TO252	6.90	10.50	2.70	1.50	1.50	16.00	1.75	7.50	8.00	4.00	2.00	0.30
(DPAK)	±0.10	±0.10	±0.10	MIN	±0.10	+0.30 -0.20	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

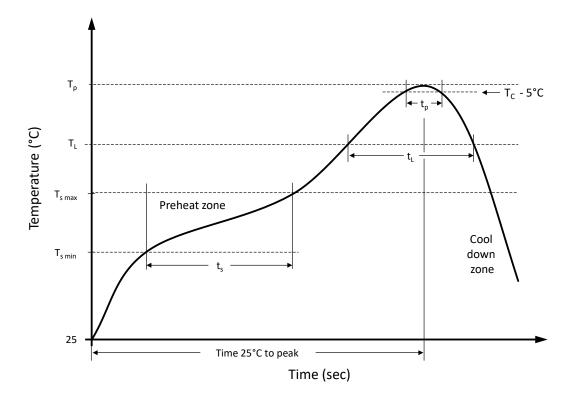


CEU16N10L ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 8





RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T_L to T_p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website <u>www.mgt.co.com.</u>